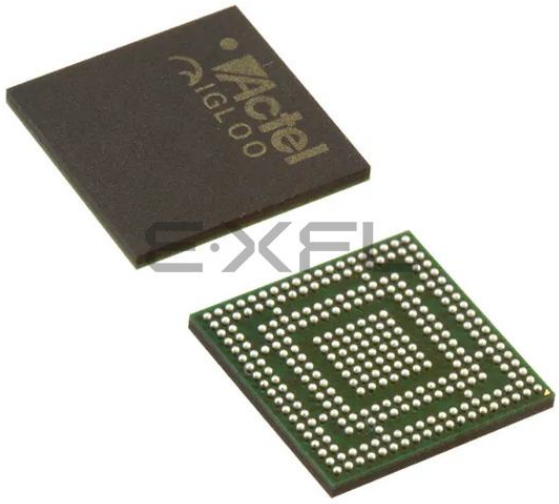

Welcome to E-XFL.COM

Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	24576
Total RAM Bits	147456
Number of I/O	215
Number of Gates	1000000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 70°C (TA)
Package / Case	281-TFBGA, CSBGA
Supplier Device Package	281-CSP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/agl1000v5-cs281

- Wide input frequency range (f_{IN_CCC}) = 1.5 MHz up to 250 MHz
- Output frequency range (f_{OUT_CCC}) = 0.75 MHz up to 250 MHz
- 2 programmable delay types for clock skew minimization
- Clock frequency synthesis (for PLL only)

Additional CCC specifications:

- Internal phase shift = 0°, 90°, 180°, and 270°. Output phase shift depends on the output divider configuration (for PLL only).
- Output duty cycle = 50% ± 1.5% or better (for PLL only)
- Low output jitter: worst case < 2.5% × clock period peak-to-peak period jitter when single global network used (for PLL only)
- Maximum acquisition time is 300 µs (for PLL only)
- Exceptional tolerance to input period jitter—allowable input jitter is up to 1.5 ns (for PLL only)
- Four precise phases; maximum misalignment between adjacent phases of 40 ps × 250 MHz / f_{OUT_CCC} (for PLL only)

Global Clocking

IGLOO devices have extensive support for multiple clocking domains. In addition to the CCC and PLL support described above, there is a comprehensive global clock distribution network.

Each VersaTile input and output port has access to nine VersaNets: six chip (main) and three quadrant global networks. The VersaNets can be driven by the CCC or directly accessed from the core via multiplexers (MUXes). The VersaNets can be used to distribute low-skew clock signals or for rapid distribution of high-fanout nets.

I/Os with Advanced I/O Standards

The IGLOO family of FPGAs features a flexible I/O structure, supporting a range of voltages (1.2 V, 1.5 V, 1.8 V, 2.5 V, 3.0 V wide range, and 3.3 V). IGLOO FPGAs support many different I/O standards—single-ended and differential.

The I/Os are organized into banks, with two or four banks per device. The configuration of these banks determines the I/O standards supported (Table 1-1).

Table 1-1 • **I/O Standards Supported**

I/O Bank Type	Device and Bank Location	I/O Standards Supported		
		LVTTL/ LVCMOS	PCI/PCI-X	LVPECL, LVDS, B-LVDS, M-LVDS
Advanced	East and west banks of AGL250 and larger devices	✓	✓	✓
Standard Plus	North and south banks of AGL250 and larger devices All banks of AGL060 and AGL125K	✓	✓	Not supported
Standard	All banks of AGL015 and AGL030	✓	Not supported	Not supported

Each I/O module contains several input, output, and enable registers. These registers allow the implementation of the following:

- Single-Data-Rate applications
- Double-Data-Rate applications—DDR LVDS, B-LVDS, and M-LVDS I/Os for point-to-point communications

IGLOO banks for the AGL250 device and above support LVPECL, LVDS, B-LVDS, and M-LVDS. B-LVDS and M-LVDS can support up to 20 loads.

Hot-swap (also called hot-plug, or hot-insertion) is the operation of hot-insertion or hot-removal of a card in a powered-up system.

Cold-sparing (also called cold-swap) refers to the ability of a device to leave system data undisturbed when the system is powered up, while the component itself is powered down, or when power supplies are floating.

Wide Range I/O Support

IGLOO devices support JEDEC-defined wide range I/O operation. IGLOO devices support both the JESD8-B specification, covering 3 V and 3.3 V supplies, for an effective operating range of 2.7 V to 3.6 V, and JESD8-12 with its 1.2 V nominal, supporting an effective operating range of 1.14 V to 1.575 V.

Wider I/O range means designers can eliminate power supplies or power conditioning components from the board or move to less costly components with greater tolerances. Wide range eases I/O bank management and provides enhanced protection from system voltage spikes, while providing the flexibility to easily run custom voltage applications.

Specifying I/O States During Programming

You can modify the I/O states during programming in FlashPro. In FlashPro, this feature is supported for PDB files generated from Designer v8.5 or greater. See the *FlashPro User Guide* for more information.

Note: PDB files generated from Designer v8.1 to Designer v8.4 (including all service packs) have limited display of Pin Numbers only.

1. Load a PDB from the FlashPro GUI. You must have a PDB loaded to modify the I/O states during programming.
2. From the FlashPro GUI, click PDB Configuration. A FlashPoint – Programming File Generator window appears.
3. Click the Specify I/O States During Programming button to display the Specify I/O States During Programming dialog box.
4. Sort the pins as desired by clicking any of the column headers to sort the entries by that header. Select the I/Os you wish to modify (Figure 1-5 on page 1-9).
5. Set the I/O Output State. You can set Basic I/O settings if you want to use the default I/O settings for your pins, or use Custom I/O settings to customize the settings for each pin. Basic I/O state settings:

   1 – I/O is set to drive out logic High

   0 – I/O is set to drive out logic Low

   Last Known State – I/O is set to the last value that was driven out prior to entering the programming mode, and then held at that value during programming

   Z -Tri-State: I/O is tristated

Table 2-26 • **Summary of Maximum and Minimum DC Input and Output Levels Applicable to Commercial and Industrial Conditions—Software Default Settings**
Applicable to Standard Plus I/O Banks

I/O Standard	Drive Strength	Equivalent Software Default Drive Strength Option[2]	Slew Rate	VIL		VIH		VOL	VOH	I_{OL}	I_{OH}
				Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA
3.3 V LVTTL / 3.3 V LVCMOS	12 mA	12 mA	High	–0.3	0.8	2	3.6	0.4	2.4	12	12
3.3 V LVCMOS Wide Range[3]	100 µA	12 mA	High	–0.3	0.8	2	3.6	0.2	VDD-0.2	0.1	0.1
2.5 V LVCMOS	12 mA	12 mA	High	–0.3	0.7	1.7	2.7	0.7	1.7	12	12
1.8 V LVCMOS	8 mA	8 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI – 0.45	8	8
1.5 V LVCMOS	4 mA	4 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	1.575	0.25 * VCCI	0.75 * VCCI	4	4
1.2 V LVCMOS[4]	2 mA	2 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	1.26	0.25 * VCCI	0.75 * VCCI	2	2
1.2 V LVCMOS Wide Range[4]	100 µA	2 mA	High	–0.3	0.3 * VCCI	0.7 * VCCI	1.575	0.1	VCCI – 0.1	0.1	0.1
3.3 V PCI	Per PCI specifications										
3.3 V PCI-X	Per PCI-X specifications										

Notes:

1. *Currents are measured at 85°C junction temperature.*
2. *The minimum drive strength for any LVCMOS 1.2 V or LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
3. *All LVMCOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.*
4. *Applicable to V2 Devices operating at VCCI ≥ VCC.*
5. *All LVCMOS 1.2 V software macros support LVCMOS 1.2 V wide range as specified in the JESD8-12 specification.*

Table 2-27 • **Summary of Maximum and Minimum DC Input and Output Levels Applicable to Commercial and Industrial Conditions—Software Default Settings**
Applicable to Standard I/O Banks

I/O Standard	Drive Strength	Equivalent Software Default Drive Strength Option[2]	Slew Rate	VIL		V_{IH}		VOL	V_{OH}	I_{OL}[1]	I_{OH}[1]
				Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA
3.3 V LVTTL / 3.3 V LVCMOS	8 mA	8 mA	High	–0.3	0.8	2	3.6	0.4	2.4	8	8
3.3 V LVCMOS Wide Range[3]	100 µA	8 mA	High	–0.3	0.8	2	3.6	0.2	VDD-0.2	0.1	0.1
2.5 V LVCMOS	8 mA	8 mA	High	–0.3	0.7	1.7	3.6	0.7	1.7	8	8
1.8 V LVCMOS	4 mA	4 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI – 0.45	4	4
1.5 V LVCMOS	2 mA	2 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	2	2
1.2 V LVCMOS[4]	1 mA	1 mA	High	–0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.25 * VCCI	0.75 * VCCI	1	1
1.2 V LVCMOS Wide Range[4,5]	100 µA	1 mA	High	–0.3	0.3 * VCCI	0.7 * VCCI	3.6	0.1	VCCI – 0.1	0.1	0.1

Notes:

1. *Currents are measured at 85°C junction temperature.*
2. *The minimum drive strength for any LVCMOS 1.2 V or LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
3. *All LVMCOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.*
4. *Applicable to V2 Devices operating at VCCI ≥ VCC.*
5. *All LVCMOS 1.2 V software macros support LVCMOS 1.2 V wide range as specified in the JESD8-12 specification.*

Table 2-31 • **Summary of I/O Timing Characteristics—Software Default Settings, Std. Speed Grade, Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI (per standard) Applicable to Advanced I/O Banks**

I/O Standard	Drive Strength	Equivalent Software Default Drive Strength Option[1] (mA)	Slew Rate	Capacitive Load (pF)	External Resistor (Ω)	t_{DOUT} (ns)	t_{DP} (ns)	t_{DIN} (ns)	t_{PY} (ns)	t_{EOUT} (ns)	t_{ZL} (ns)	t_{ZH} (ns)	t_{LZ} (ns)	t_{HZ} (ns)	t_{ZLS} (ns)	t_{ZHS} (ns)	Units
3.3 V LVTTL / 3.3 V LVCMOS	12 mA	12	High	5	–	0.97	2.09	0.18	0.85	0.66	2.14	1.68	2.67	3.05	5.73	5.27	ns
3.3 V LVCMOS Wide Range[2]	100 µA	12	High	5	–	0.97	2.93	0.18	1.19	0.66	2.95	2.27	3.81	4.30	6.54	5.87	ns
2.5 V LVCMOS	12 mA	12	High	5	–	0.97	2.09	0.18	1.08	0.66	2.14	1.83	2.73	2.93	5.73	5.43	ns
1.8 V LVCMOS	12 mA	12	High	5	–	0.97	2.24	0.18	1.01	0.66	2.29	2.00	3.02	3.40	5.88	5.60	ns
1.5 V LVCMOS	12 mA	12	High	5	–	0.97	2.50	0.18	1.17	0.66	2.56	2.27	3.21	3.48	6.15	5.86	ns
3.3 V PCI	Per PCI spec	–	High	10	25 [2]	0.97	2.32	0.18	0.74	0.66	2.37	1.78	2.67	3.05	5.96	5.38	ns
3.3 V PCI-X	Per PCI-X spec	–	High	10	25 [2]	0.97	2.32	0.19	0.70	0.66	2.37	1.78	2.67	3.05	5.96	5.38	ns
LVDS	24 mA	–	High	–	–	0.97	1.74	0.19	1.35	–	–	–	–	–	–	–	ns
LVPECL	24 mA	–	High	–	–	0.97	1.68	0.19	1.16	–	–	–	–	–	–	–	ns

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.*
3. *Resistance is used to measure I/O propagation delays as defined in PCI specifications. See Figure 2-12 on page 2-79 for connectivity. This resistor is not required during normal operation.*
4. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

Table 2-34 • **Summary of I/O Timing Characteristics—Software Default Settings, Std. Speed Grade, Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI (per standard) Applicable to Advanced I/O Banks**

I/O Standard	Drive Strength	Equivalent Software Default Drive Strength Option[1]	Slew Rate	Capacitive Load (pF)	External Resistor (Ω)	t_{DOUT} (ns)	t_{DP} (ns)	t_{DIN} (ns)	t_{PY} (ns)	t_{EOUT} (ns)	t_{ZL} (ns)	t_{ZH} (ns)	t_{LZ} (ns)	t_{HZ} (ns)	t_{ZLS} (ns)	t_{ZHS} (ns)	Units
3.3 V LVTTL / 3.3 V LVCMOS	12 mA	12 mA	High	5	–	1.55	2.67	0.26	0.98	1.10	2.71	2.18	3.25	3.93	8.50	7.97	ns
3.3 V LVCMOS Wide Range[2]	100 µA	12 mA	High	5	–	1.55	3.73	0.26	1.32	1.10	3.73	2.91	4.51	5.43	9.52	8.69	ns
2.5 V LVCMOS	12 mA	12 mA	High	5	–	1.55	2.64	0.26	1.20	1.10	2.67	2.29	3.30	3.79	8.46	8.08	ns
1.8 V LVCMOS	12 mA	12 mA	High	5	–	1.55	2.72	0.26	1.11	1.10	2.76	2.43	3.58	4.19	8.55	8.22	ns
1.5 V LVCMOS	12 mA	12 mA	High	5	–	1.55	2.96	0.26	1.27	1.10	3.00	2.70	3.75	4.23	8.78	8.48	ns
1.2 V LVCMOS	2 mA	2 mA	High	5	–	1.55	3.60	0.26	1.60	1.10	3.47	3.36	3.93	3.65	9.26	9.14	ns
1.2 V LVCMOS Wide Range[3]	100 µA	2 mA	High	5	–	1.55	3.60	0.26	1.60	1.10	3.47	3.36	3.93	3.65	9.26	9.14	ns
3.3 V PCI	Per PCI spec	–	High	10	25[2]	1.55	2.91	0.26	0.86	1.10	2.95	2.29	3.25	3.93	8.74	8.08	ns
3.3 V PCI-X	Per PCI-X spec	–	High	10	25[2]	1.55	2.91	0.25	0.86	1.10	2.95	2.29	3.25	3.93	8.74	8.08	ns
LVDS	24 mA	–	High	–	–	1.55	2.27	0.25	1.57	–	–	–	–	–	–	–	ns
LVPECL	24 mA	–	High	–	–	1.55	2.24	0.25	1.38	–	–	–	–	–	–	–	ns

Notes:

1. *The minimum drive strength for any LVCMOS 1.2 V or LVCMOS 3.3 V software configuration when run in wide range is ±100 µA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.*
3. *All LVCMOS 1.2 V software macros support LVCMOS 1.2 V wide range as specified in the JESD8-12 specification*
4. *Resistance is used to measure I/O propagation delays as defined in PCI specifications. See Figure 2-12 on page 2-79 for connectivity. This resistor is not required during normal operation.*
5. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

Table 2-43 • **I/O Short Currents IOSH/IOSL**
Applicable to Standard Plus I/O Banks

	Drive Strength	IOSL (mA)*	IOSH (mA)*
3.3 V LVTTL / 3.3 V LVCMOS	2 mA	25	27
	4 mA	25	27
	6 mA	51	54
	8 mA	51	54
	12 mA	103	109
	16 mA	103	109
3.3 V LVCMOS Wide Range	100 µA	Same as regular 3.3 V LVCMOS	Same as regular 3.3 V LVCMOS
2.5 V LVCMOS	2 mA	16	18
	4 mA	16	18
	6 mA	32	37
	8 mA	32	37
	12 mA	65	74
1.8 V LVCMOS	2 mA	9	11
	4 mA	17	22
	6 mA	35	44
	8 mA	35	44
1.5 V LVCMOS	2 mA	13	16
	4 mA	25	33
1.2 V LVCMOS	2 mA	20	26
1.2 V LVCMOS Wide Range	100 µA	20	26
3.3 V PCI/PCI-X	Per PCI/PCI-X specification	103	109

*Note: *T_J = 100°C*

Timing Characteristics

Applies to 1.5 V DC Core Voltage

Table 2-67 • 3.3 V LVCMOS Wide Range Low Slew – Applies to 1.5 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.7 V
Applicable to Advanced Banks

Drive Strength	Equivalent Software Default Drive Strength Option[1]	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
100 µA	2 mA	Std.	0.97	6.61	0.18	1.19	0.66	6.63	5.63	3.15	2.98	10.22	9.23	ns
100 µA	4 mA	Std.	0.97	6.61	0.18	1.19	0.66	6.63	5.63	3.15	2.98	10.22	9.23	ns
100 µA	6 mA	Std.	0.97	5.49	0.18	1.19	0.66	5.51	4.84	3.54	3.66	9.10	8.44	ns
100 µA	8 mA	Std.	0.97	5.49	0.18	1.19	0.66	5.51	4.84	3.54	3.66	9.10	8.44	ns
100 µA	12 mA	Std.	0.97	4.69	0.18	1.19	0.66	4.71	4.25	3.80	4.10	8.31	7.85	ns
100 µA	16 mA	Std.	0.97	4.46	0.18	1.19	0.66	4.48	4.11	3.86	4.21	8.07	7.71	ns
100 µA	24 mA	Std.	0.97	4.34	0.18	1.19	0.66	4.36	4.14	3.93	4.64	7.95	7.74	ns

Notes:

1. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ± 100 µA. Drive strengths displayed in software are supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

Table 2-68 • 3.3 V LVCMOS Wide Range High Slew – Applies to 1.5 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.7 V
Applicable to Advanced Banks

Drive Strength	Equivalent Software Default Drive Strength Option[1]	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
100 µA	2 mA	Std.	0.97	3.92	0.18	1.19	0.66	3.94	3.10	3.16	3.17	7.54	6.70	ns
100 µA	4 mA	Std.	0.97	3.92	0.18	1.19	0.66	3.94	3.10	3.16	3.17	7.54	6.70	ns
100 µA	6 mA	Std.	0.97	3.28	0.18	1.19	0.66	3.30	2.54	3.54	3.86	6.90	6.14	ns
100 µA	8 mA	Std.	0.97	3.28	0.18	1.19	0.66	3.30	2.54	3.54	3.86	6.90	6.14	ns
100 µA	12 mA	Std.	0.97	2.93	0.18	1.19	0.66	2.95	2.27	3.81	4.30	6.54	5.87	ns
100 µA	16 mA	Std.	0.97	2.87	0.18	1.19	0.66	2.89	2.22	3.86	4.41	6.49	5.82	ns
100 µA	24 mA	Std.	0.97	2.90	0.18	1.19	0.66	2.92	2.16	3.94	4.86	6.51	5.75	ns

Notes:

1. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*
2. *Software default selection highlighted in gray.*
3. *The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ± 100 µA. Drive strengths displayed in software are supported for normal range only. For a detailed I/V curve, refer to the IBIS models.*

Table 2-104 • 1.8 V LVCMOS High Slew – Applies to 1.5 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 1.7 V
Applicable to Standard Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	2.62	0.18	0.98	0.66	2.67	2.59	1.67	1.29	2.62	ns
4 mA	Std.	2.18	0.18	0.98	0.66	2.22	1.93	1.97	2.06	2.18	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

1.2 V DC Core Voltage

Table 2-105 • 1.8 V LVCMOS Low Slew – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.7 V
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	1.55	6.97	0.26	1.11	1.10	7.08	6.48	2.87	2.29	12.87	12.27	ns
4 mA	Std.	1.55	5.91	0.26	1.11	1.10	6.01	5.57	3.21	3.14	11.79	11.36	ns
6 mA	Std.	1.55	5.16	0.26	1.11	1.10	5.24	4.95	3.45	3.55	11.03	10.74	ns
8 mA	Std.	1.55	4.90	0.26	1.11	1.10	4.98	4.81	3.50	3.66	10.77	10.60	ns
12 mA	Std.	1.55	4.83	0.26	1.11	1.10	4.90	4.83	3.58	4.08	10.68	10.61	ns
16 mA	Std.	1.55	4.83	0.26	1.11	1.10	4.90	4.83	3.58	4.08	10.68	10.61	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-106 • 1.8 V LVCMOS High Slew – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 1.7 V
Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	1.55	3.73	0.26	1.11	1.10	3.71	3.73	2.86	2.34	9.49	9.51	ns
4 mA	Std.	1.55	3.12	0.26	1.11	1.10	3.16	2.97	3.21	3.22	8.95	8.75	ns
6 mA	Std.	1.55	2.79	0.26	1.11	1.10	2.83	2.59	3.45	3.65	8.62	8.38	ns
8 mA	Std.	1.55	2.73	0.26	1.11	1.10	2.77	2.52	3.50	3.75	8.56	8.30	ns
12 mA	Std.	1.55	2.72	0.26	1.11	1.10	2.76	2.43	3.58	4.19	8.55	8.22	ns
16 mA	Std.	1.55	2.72	0.26	1.11	1.10	2.76	2.43	3.58	4.19	8.55	8.22	ns

Notes:

1. *Software default selection highlighted in gray.*
2. *For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.*

1.5 V LVCMOS (JESD8-11)

Low-Voltage CMOS for 1.5 V is an extension of the LVCMOS standard (JESD8-5) used for general-purpose 1.5 V applications. It uses a 1.5 V input buffer and a push-pull output buffer.

Table 2-111 • Minimum and Maximum DC Input and Output Levels Applicable to Advanced I/O Banks

1.5 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSH	IOSL	IIL[1]	IIH[2]
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[3]	Max. mA[3]	µA[4]	µA[4]
2 mA	–0.3	0.35 * VCCI	0.65 * VCCI	1.575	0.25 * VCCI	0.75 * VCCI	2	2	13	16	10	10
4 mA	–0.3	0.35 * VCCI	0.65 * VCCI	1.575	0.25 * VCCI	0.75 * VCCI	4	4	25	33	10	10
6 mA	–0.3	0.35 * VCCI	0.65 * VCCI	1.575	0.25 * VCCI	0.75 * VCCI	6	6	32	39	10	10
8 mA	–0.3	0.35 * VCCI	0.65 * VCCI	1.575	0.25 * VCCI	0.75 * VCCI	8	8	66	55	10	10
12 mA	–0.3	0.35 * VCCI	0.65 * VCCI	1.575	0.25 * VCCI	0.75 * VCCI	12	12	66	55	10	10

Notes:

1. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
2. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges*
3. *Currents are measured at 100°C junction temperature and maximum voltage.*
4. *Currents are measured at 85°C junction temperature.*
5. *Software default selection highlighted in gray.*

Table 2-112 • Minimum and Maximum DC Input and Output Levels Applicable to Standard Plus I/O Banks

1.5 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSH	IOSL	IIL[1]	IIH[2]
Drive Strength	Min. V	Max. V	Min. V	Max. V	Max. V	Min. V	mA	mA	Max. mA[3]	Max. mA[3]	µA[4]	µA[4]
2 mA	–0.3	0.35 * VCCI	0.65 * VCCI	1.575	0.25 * VCCI	0.75 * VCCI	2	2	13	16	10	10
4 mA	–0.3	0.35 * VCCI	0.65 * VCCI	1.575	0.25 * VCCI	0.75 * VCCI	4	4	25	33	10	10

Notes:

1. *IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.*
2. *IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges*
3. *Currents are measured at 100°C junction temperature and maximum voltage.*
4. *Currents are measured at 85°C junction temperature.*
5. *Software default selection highlighted in gray.*

Table 2-156 • **Parameter Definition and Measuring Nodes**

Parameter Name	Parameter Definition	Measuring Nodes (from, to)*
t_{OCLKQ}	Clock-to-Q of the Output Data Register	HH, DOUT
t_{OSUD}	Data Setup Time for the Output Data Register	FF, HH
t_{OHD}	Data Hold Time for the Output Data Register	FF, HH
t_{OSUE}	Enable Setup Time for the Output Data Register	GG, HH
t_{OHE}	Enable Hold Time for the Output Data Register	GG, HH
t_{OCLR2Q}	Asynchronous Clear-to-Q of the Output Data Register	LL, DOUT
$t_{OREMCLR}$	Asynchronous Clear Removal Time for the Output Data Register	LL, HH
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Data Register	LL, HH
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	HH, EOUT
t_{OESUD}	Data Setup Time for the Output Enable Register	JJ, HH
t_{OEHD}	Data Hold Time for the Output Enable Register	JJ, HH
t_{OESUE}	Enable Setup Time for the Output Enable Register	KK, HH
t_{OEHE}	Enable Hold Time for the Output Enable Register	KK, HH
$t_{OECLR2Q}$	Asynchronous Clear-to-Q of the Output Enable Register	II, EOUT
$t_{OEREMCLR}$	Asynchronous Clear Removal Time for the Output Enable Register	II, HH
$t_{ORECCLR}$	Asynchronous Clear Recovery Time for the Output Enable Register	II, HH
t_{ICLKQ}	Clock-to-Q of the Input Data Register	AA, EE
t_{ISUD}	Data Setup Time for the Input Data Register	CC, AA
t_{IHD}	Data Hold Time for the Input Data Register	CC, AA
t_{ISUE}	Enable Setup Time for the Input Data Register	BB, AA
t_{IHE}	Enable Hold Time for the Input Data Register	BB, AA
t_{ICLR2Q}	Asynchronous Clear-to-Q of the Input Data Register	DD, EE
$t_{IREMCLR}$	Asynchronous Clear Removal Time for the Input Data Register	DD, AA
$t_{IRECCLR}$	Asynchronous Clear Recovery Time for the Input Data Register	DD, AA

*Note: *See Figure 2-17 on page 2-86 for more information.*

1.2 V DC Core Voltage

Table 2-158 • Input Data Register Propagation Delays
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V

Parameter	Description	Std.	Units
t_{ICLKQ}	Clock-to-Q of the Input Data Register	0.68	ns
t_{ISUD}	Data Setup Time for the Input Data Register	0.97	ns
t_{IHD}	Data Hold Time for the Input Data Register	0.00	ns
t_{ISUE}	Enable Setup Time for the Input Data Register	1.02	ns
t_{IHE}	Enable Hold Time for the Input Data Register	0.00	ns
t_{ICLR2Q}	Asynchronous Clear-to-Q of the Input Data Register	1.19	ns
t_{IPRE2Q}	Asynchronous Preset-to-Q of the Input Data Register	1.19	ns
$t_{IREMCLR}$	Asynchronous Clear Removal Time for the Input Data Register	0.00	ns
$t_{IRECCLR}$	Asynchronous Clear Recovery Time for the Input Data Register	0.24	ns
$t_{IREMPRE}$	Asynchronous Preset Removal Time for the Input Data Register	0.00	ns
$t_{IRECPRE}$	Asynchronous Preset Recovery Time for the Input Data Register	0.24	ns
t_{IWCLR}	Asynchronous Clear Minimum Pulse Width for the Input Data Register	0.19	ns
t_{IWPRE}	Asynchronous Preset Minimum Pulse Width for the Input Data Register	0.19	ns
$t_{ICKMPWH}$	Clock Minimum Pulse Width High for the Input Data Register	0.31	ns
$t_{ICKMPWL}$	Clock Minimum Pulse Width Low for the Input Data Register	0.28	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Output Register

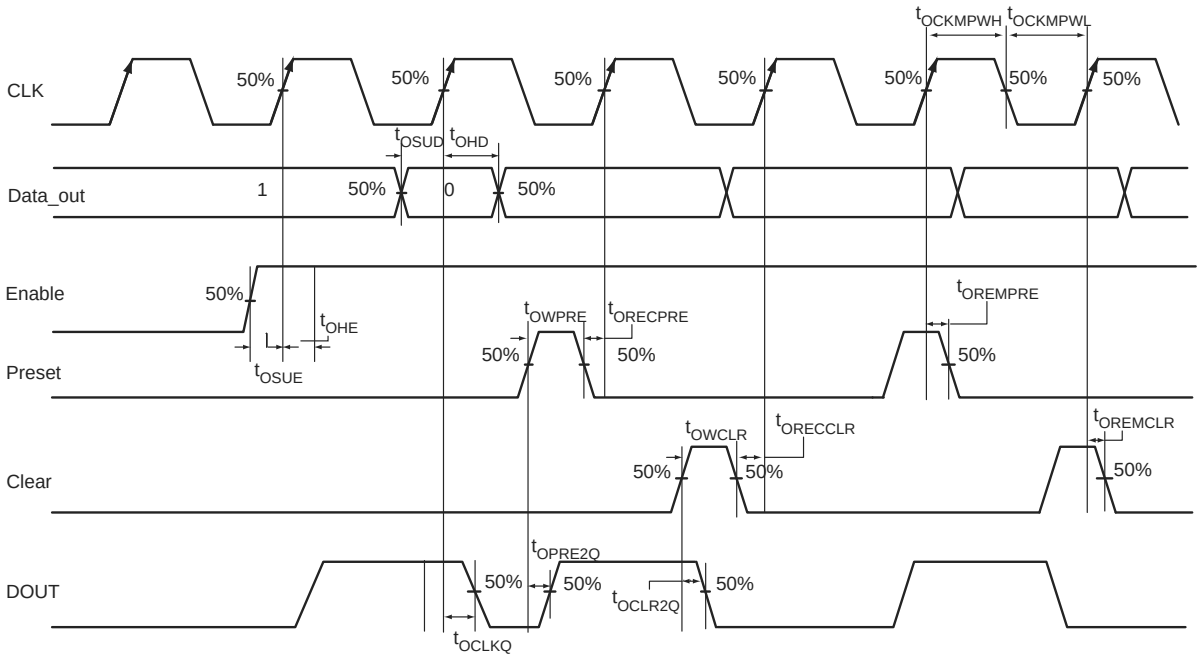

Figure 2-19 • Output Register Timing Diagram

Table 2-177 • **AGL250 Global Resource**
Commercial-Case Conditions: T_J = 70°C, VCC = 1.425 V

Parameter	Description	Std.		Units
		Min.[1]	Max.[2]	
t_{RCKL}	Input Low Delay for Global Clock	1.39	1.73	ns
t_{RCKH}	Input High Delay for Global Clock	1.41	1.84	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	1.18		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	1.15		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.43	ns

Notes:

1. *Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).*
2. *Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).*
3. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

Table 2-178 • **AGL400 Global Resource**
Commercial-Case Conditions: T_J = 70°C, VCC = 1.425 V

Parameter	Description	Std.		Units
		Min. [1]	Max. [2]	
t_{RCKL}	Input Low Delay for Global Clock	1.45	1.79	ns
t_{RCKH}	Input High Delay for Global Clock	1.48	1.91	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	1.18		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	1.15		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.43	ns

Notes:

1. *Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).*
2. *Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).*
3. *For specific junction temperature and voltage-supply levels, refer to Table 2-6 on page 2-7 for derating values.*

1.2 V DC Core Voltage

***Table 2-193* • RAM4K9**
Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.14 V

Parameter	Description	Std.	Units
t_{AS}	Address setup time	1.53	ns
t_{AH}	Address hold time	0.29	ns
t_{ENS}	REN WEN setup time	1.50	ns
t_{ENH}	REN, WEN hold time	0.29	ns
t_{BKS}	BLK setup time	3.05	ns
t_{BKH}	BLK hold time	0.29	ns
t_{DS}	Input data (DIN) setup time	1.33	ns
t_{DH}	Input data (DIN) hold time	0.66	ns
t_{CKQ1}	Clock High to new data valid on DOUT (output retained, WMODE = 0)	6.61	ns
	Clock High to new data valid on DOUT (flow-through, WMODE = 1)	5.72	ns
t_{CKQ2}	Clock High to new data valid on DOUT (pipelined)	3.38	ns
t_{C2CWWL}[1]	Address collision clk-to-clk delay for reliable write after write on same address – Applicable to Closing Edge	0.30	ns
t_{C2CRWH}[1]	Address collision clk-to-clk delay for reliable read access after write on same address – Applicable to Opening Edge	0.89	ns
t_{C2CWRH}[1]	Address collision clk-to-clk delay for reliable write access after read on same address – Applicable to Opening Edge	1.01	ns
t_{RSTBQ}	RESET Low to data out Low on DOUT (flow-through)	3.86	ns
	RESET Low to data out Low on DOUT (pipelined)	3.86	ns
$t_{REMRSTB}$	RESET removal	1.12	ns
$t_{RECRSTB}$	RESET recovery	5.93	ns
$t_{MPWRSTB}$	RESET minimum pulse width	1.18	ns
t_{CYC}	Clock cycle time	10.90	ns
F_{MAX}	Maximum frequency	92	MHz

Notes:

1. *For more information, refer to the application note* Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs.
2. *For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.*

1.2 V DC Core Voltage

***Table 2-196* • FIFO**
Worst Commercial-Case Conditions: T_J = 70°C, VCC = 1.14 V

Parameter	Description	Std.	Units
t_{ENS}	REN, WEN Setup Time	4.13	ns
t_{ENH}	REN, WEN Hold Time	0.31	ns
t_{BKS}	BLK Setup Time	0.47	ns
t_{BKH}	BLK Hold Time	0.00	ns
t_{DS}	Input Data (WD) Setup Time	1.56	ns
t_{DH}	Input Data (WD) Hold Time	0.49	ns
t_{CKQ1}	Clock High to New Data Valid on RD (flow-through)	6.80	ns
t_{CKQ2}	Clock High to New Data Valid on RD (pipelined)	3.62	ns
t_{RCKEF}	RCLK High to Empty Flag Valid	7.23	ns
t_{WCKFF}	WCLK High to Full Flag Valid	6.85	ns
t_{CKAF}	Clock High to Almost Empty/Full Flag Valid	26.61	ns
t_{RSTFG}	RESET Low to Empty/Full Flag Valid	7.12	ns
t_{RSTAF}	RESET Low to Almost Empty/Full Flag Valid	26.33	ns
t_{RSTBQ}	RESET Low to Data Out Low on RD (flow-through)	4.09	ns
	RESET Low to Data Out Low on RD (pipelined)	4.09	ns
$t_{REMRSTB}$	RESET Removal	1.23	ns
$t_{RECRSTB}$	RESET Recovery	6.58	ns
$t_{MPWRSTB}$	RESET Minimum Pulse Width	1.18	ns
t_{CYC}	Clock Cycle Time	10.90	ns
F_{MAX}	Maximum Frequency for FIFO	92	MHz

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

CS281	
Pin Number	**AGL1000 Function**
A1	GND
A2	GAB0/IO02RSB0
A3	GAC1/IO05RSB0
A4	IO13RSB0
A5	IO11RSB0
A6	IO16RSB0
A7	IO20RSB0
A8	IO24RSB0
A9	IO29RSB0
A10	VCCIB0
A11	IO39RSB0
A12	IO45RSB0
A13	IO48RSB0
A14	IO58RSB0
A15	IO61RSB0
A16	IO62RSB0
A17	GBC1/IO73RSB0
A18	GBA0/IO76RSB0
A19	GND
B1	GAA2/IO225PPB3
B2	VCCIB0
B3	GAB1/IO03RSB0
B4	GAC0/IO04RSB0
B5	IO12RSB0
B6	GND
B7	IO21RSB0
B8	IO26RSB0
B9	IO34RSB0
B10	IO35RSB0
B11	IO36RSB0
B12	IO46RSB0
B13	IO52RSB0
B14	GND
B15	IO59RSB0
B16	GBC0/IO72RSB0
B17	GBA1/IO77RSB0

CS281	
Pin Number	**AGL1000 Function**
B18	VCCIB1
B19	IO79NDB1
C1	GAB2/IO224PPB3
C2	IO225NPB3
C6	IO18RSB0
C14	IO63RSB0
C18	IO78NPB1
C19	GBB2/IO79PDB1
D1	IO219PPB3
D2	IO223NPB3
D4	GAA0/IO00RSB0
D5	GAA1/IO01RSB0
D6	IO15RSB0
D7	IO19RSB0
D8	IO27RSB0
D9	IO32RSB0
D10	GND
D11	IO38RSB0
D12	IO44RSB0
D13	IO47RSB0
D14	IO60RSB0
D15	GBB0/IO74RSB0
D16	GBA2/IO78PPB1
D18	GBC2/IO80PPB1
D19	IO88NPB1
E1	IO217NPB3
E2	IO221PPB3
E4	IO221NPB3
E5	IO10RSB0
E6	IO14RSB0
E7	IO25RSB0
E8	IO28RSB0
E9	IO31RSB0
E10	IO33RSB0
E11	IO42RSB0
E12	IO49RSB0

CS281	
Pin Number	**AGL1000 Function**
E13	IO53RSB0
E14	GBB1/IO75RSB0
E15	IO80NPB1
E16	IO85PPB1
E18	IO83PPB1
E19	IO84NPB1
F1	IO214NPB3
F2	GND
F3	IO217PPB3
F4	IO219NPB3
F5	IO224NPB3
F15	IO85NPB1
F16	IO84PPB1
F17	IO83NPB1
F18	GND
F19	IO90PPB1
G1	IO212NPB3
G2	IO211NDB3
G4	IO214PPB3
G5	IO212PPB3
G7	GAC2/IO223PPB3
G8	VCCIB0
G9	IO30RSB0
G10	IO37RSB0
G11	IO43RSB0
G12	VCCIB0
G13	IO88PPB1
G15	IO89NDB1
G16	IO89PDB1
G18	GCC0/IO91NPB1
G19	GCB1/IO92PPB1
H1	GFB0/IO208NPB3
H2	IO211PDB3
H4	GFC1/IO209PPB3
H5	GFB1/IO208PPB3
H7	VCCIB3

CS281	
Pin Number	**AGL1000 Function**
R15	IO122RSB2
R16	GDA1/IO113PPB1
R18	GDB0/IO112NPB1
R19	GDC0/IO111NPB1
T1	IO197PPB3
T2	GEC0/IO190NPB3
T4	GEB0/IO189NPB3
T5	IO181RSB2
T6	IO172RSB2
T7	IO171RSB2
T8	IO156RSB2
T9	IO159RSB2
T10	GND
T11	IO139RSB2
T12	IO138RSB2
T13	IO129RSB2
T14	IO123RSB2
T15	GDC2/IO116RSB2
T16	TMS
T18	VJTAG
T19	GDB1/IO112PPB1
U1	IO193PDB3
U2	GEA1/IO188PPB3
U6	IO167RSB2
U14	IO128RSB2
U18	TRST
U19	GDA0/IO113NPB1
V1	IO193NDB3
V2	VCCIB3
V3	GEC2/IO185RSB2
V4	IO182RSB2
V5	IO175RSB2
V6	GND
V7	IO161RSB2
V8	IO143RSB2
V9	IO146RSB2

CS281	
Pin Number	**AGL1000 Function**
V10	IO145RSB2
V11	IO144RSB2
V12	IO134RSB2
V13	IO133RSB2
V14	GND
V15	IO119RSB2
V16	GDA2/IO114RSB2
V17	TDI
V18	VCCIB2
V19	TDO
W1	GND
W2	FF/GEB2/IO186RSB2
W3	IO183RSB2
W4	IO176RSB2
W5	IO170RSB2
W6	IO162RSB2
W7	IO157RSB2
W8	IO152RSB2
W9	IO149RSB2
W10	VCCIB2
W11	IO140RSB2
W12	IO135RSB2
W13	IO130RSB2
W14	IO125RSB2
W15	IO120RSB2
W16	IO118RSB2
W17	GDB2/IO115RSB2
W18	TCK
W19	GND

QN132	
Pin Number	**AGL250 Function**
C17	IO74RSB2
C18	VCCIB2
C19	TCK
C20	VMV2
C21	VPUMP
C22	VJTAG
C23	VCCIB1
C24	IO53NSB1
C25	IO51NPB1
C26	GCA1/IO50PPB1
C27	GCC0/IO48NDB1
C28	VCCIB1
C29	IO42NDB1
C30	GNDQ
C31	GBA1/IO40RSB0
C32	GBB0/IO37RSB0
C33	VCC
C34	IO24RSB0
C35	IO19RSB0
C36	IO16RSB0
C37	IO10RSB0
C38	VCCIB0
C39	GAB1/IO03RSB0
C40	VMV0
D1	GND
D2	GND
D3	GND
D4	GND

FG484	
Pin Number	**AGL1000 Function**
C21	NC
C22	VCCIB1
D1	IO219PDB3
D2	IO220NDB3
D3	NC
D4	GND
D5	GAA0/IO00RSB0
D6	GAA1/IO01RSB0
D7	GAB0/IO02RSB0
D8	IO16RSB0
D9	IO22RSB0
D10	IO28RSB0
D11	IO35RSB0
D12	IO45RSB0
D13	IO50RSB0
D14	IO55RSB0
D15	IO61RSB0
D16	GBB1/IO75RSB0
D17	GBA0/IO76RSB0
D18	GBA1/IO77RSB0
D19	GND
D20	NC
D21	NC
D22	NC
E1	IO219NDB3
E2	NC
E3	GND
E4	GAB2/IO224PDB3
E5	GAA2/IO225PDB3
E6	GNDQ
E7	GAB1/IO03RSB0
E8	IO17RSB0
E9	IO21RSB0
E10	IO27RSB0
E11	IO34RSB0
E12	IO44RSB0

Revision / Version	Changes	Page
Revision 8 (cont'd)	Table 2-13 • Summary of I/O Input Buffer Power (per pin) – Default I/O Software Settings, Table 2-14 • Summary of I/O Input Buffer Power (per pin) – Default I/O Software Settings, Table 2-15 • Summary of I/O Input Buffer Power (per pin) – Default I/O Software Settings, and Table 2-16 • Summary of I/O Output Buffer Power (per pin) – Default I/O Software Settings1 were updated to change PDC2 to PDC6 and PDC3 to PDC7. The table notes were updated to reflect that power was measured on VCCI.	2-10 through 2-11
	In Table 2-19 • Different Components Contributing to Dynamic Power Consumption in IGLOO Devices, the description for PAC13 was changed from Static to Dynamic.	2-13
	Table 2-20 • Different Components Contributing to the Static Power Consumption in IGLOO Devices and Table 2-22 • Different Components Contributing to the Static Power Consumption in IGLOO Device were updated to add PDC6 and PDC7, and to change the definition for PDC5 to bank quiescent power. Subtitles were added to indicate type of devices and core supply voltage.	2-14, 2-16
	The "Total Static Power Consumption—PSTAT" section was updated to revise the calculation of P_{STAT}, including PDC6 and PDC7.	2-17
	Footnote † was updated to include information about PAC13. The PLL Contribution equation was changed from: $P_{PLL} = P_{AC13} + P_{AC14} * F_{CLKOUT}$ to $P_{PLL} = P_{DC4} + P_{AC13} * F_{CLKOUT}$.	2-18
Revision 7 (Jun 2008) Packaging v1.5	The "QN132" package diagram was updated to include D1 to D4. In addition, note 1 was changed from top view to bottom view, and note 2 is new.	4-28
Revision 6 (Jun 2008) Packaging v1.4	This document was divided into two sections and given a version number, starting at v1.0. The first section of the document includes features, benefits, ordering information, and temperature and speed grade offerings. The second section is a device family overview.	N/A
	Pin numbers were added to the "QN68" package diagram. Note 2 was added below the diagram.	4-25
Revision 5 (Mar 2008) Packaging v1.3	The "CS196" package and pin table was added for AGL250.	4-12
Revision 4 (Mar 2008) Product Brief v1.0	The "Low Power" section was updated to change "1.2 V and 1.5 V Core Voltage" to "1.2 V and 1.5 V Core and I/O Voltage." The text "(from 12 µW)" was removed from "Low Power Active FPGA Operation."	I
	1.2_V was added to the list of core and I/O voltages in the "Advanced I/O" and "I/Os with Advanced I/O Standards" section sections.	I, 1-7
	The "Embedded Memory" section was updated to remove the footnote reference from the section heading and place it instead after "4,608-Bit" and "True Dual-Port SRAM (except ×18)."	I